

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

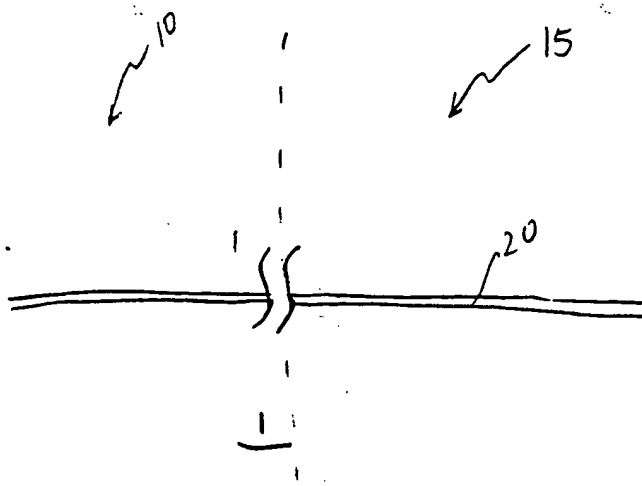


FIG. 1A (PRIOR ART)

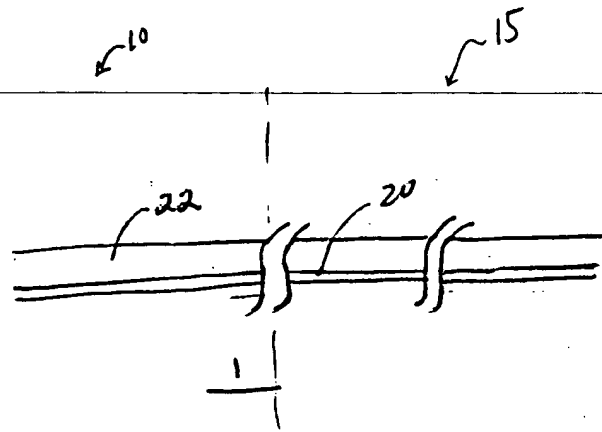


FIG. 1B (PRIOR ART)

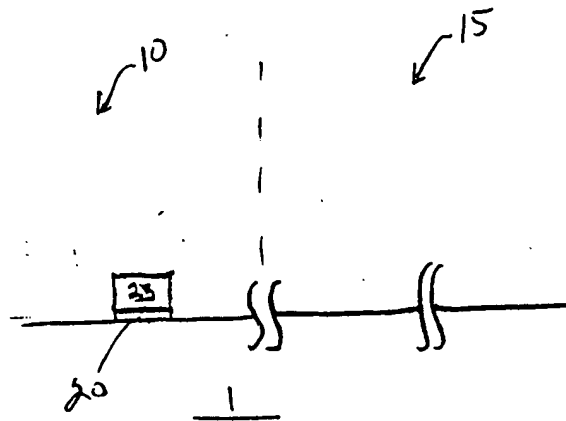


FIG. 1C (PRIOR ART)

2025 RELEASE UNDER E.O. 14176

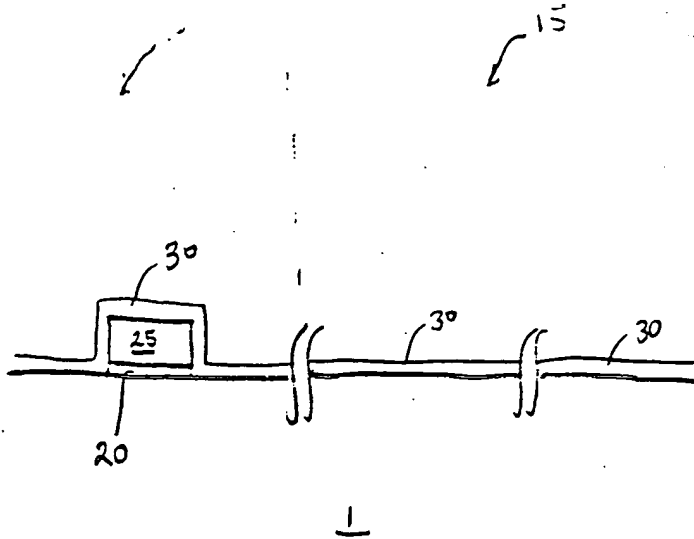


FIG. 1D (PRIOR ART)

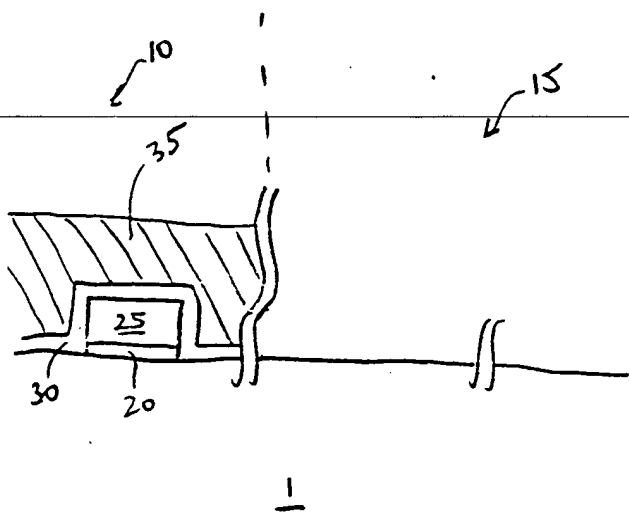


FIG. 1E (PRIOR ART)

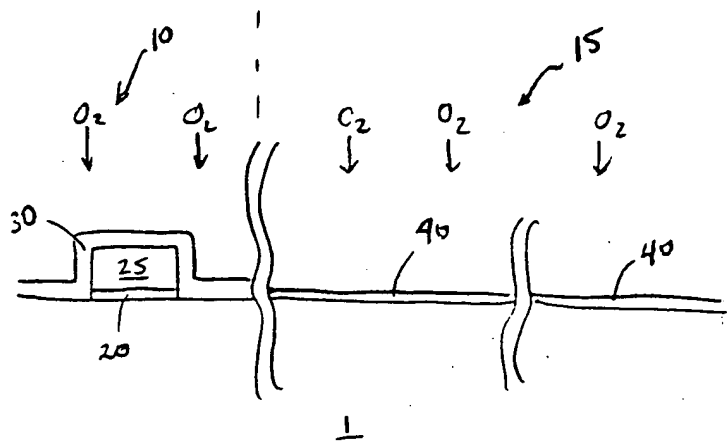


FIG. 1F (PRIOR ART)

09216073-121898

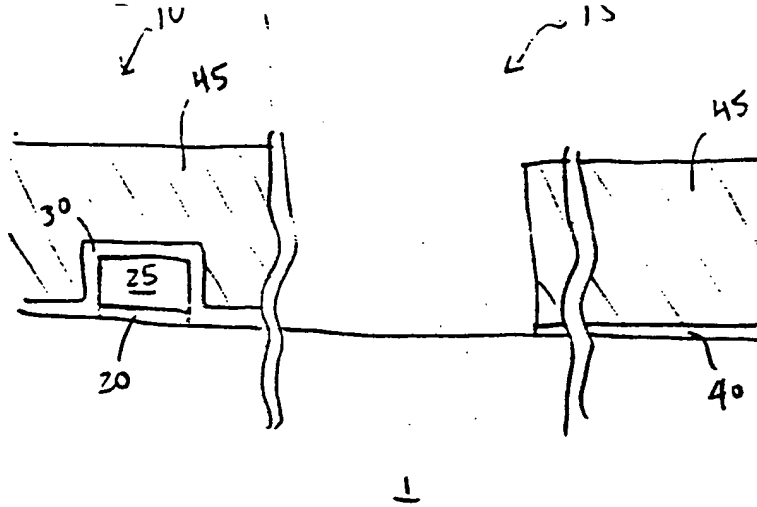


FIG. 1G (PRIOR ART)

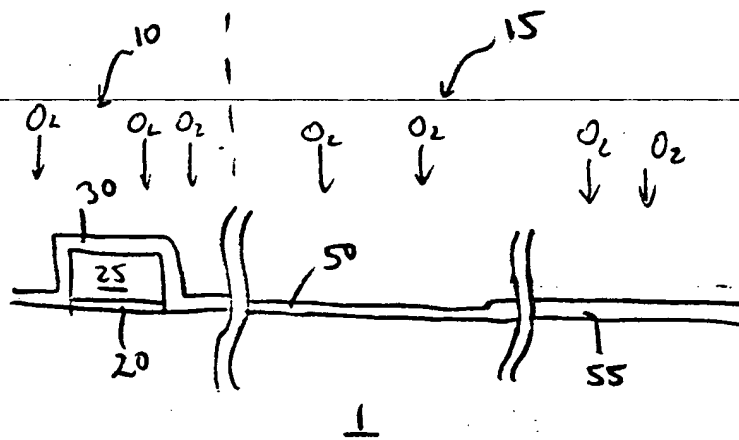


FIG. 1H (PRIOR ART)

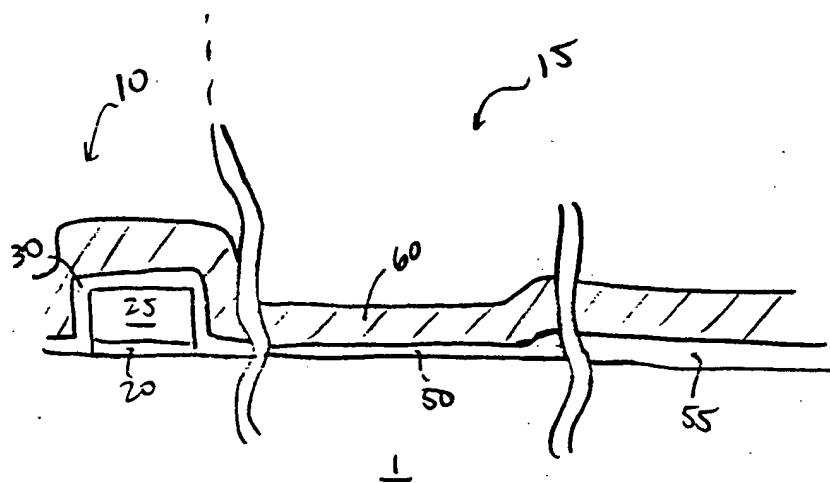


FIG. 1I (PRIOR ART)

09216078-121898

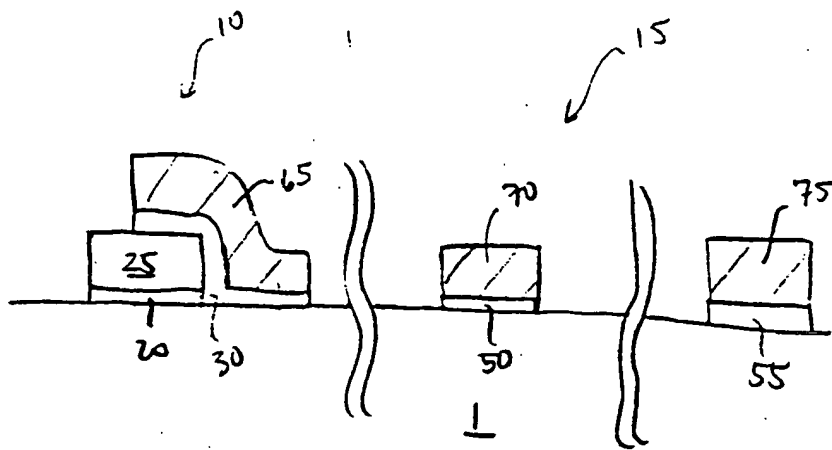


FIG. 1J (PRIOR ART)

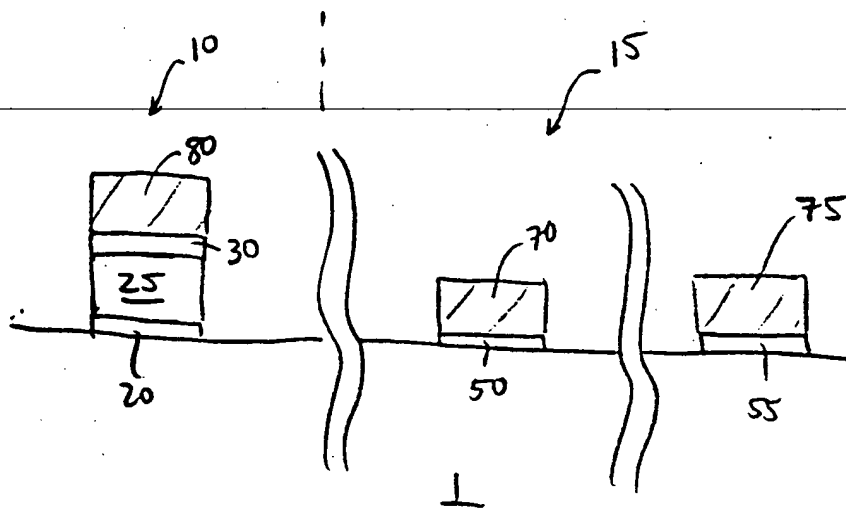


FIG. 1K (PRIOR ART)

09216078 124899

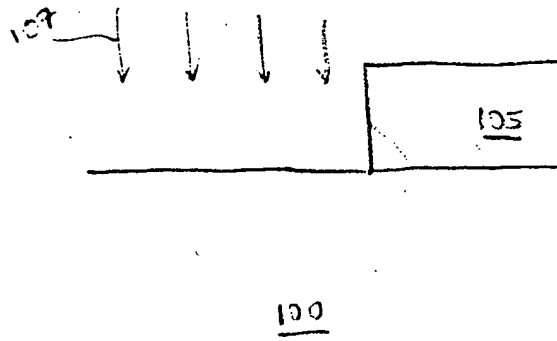


FIG. 2A

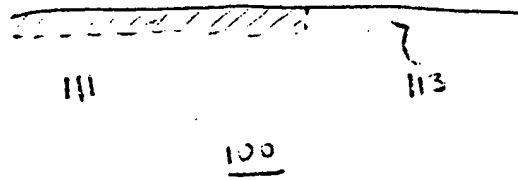


FIG. 2B

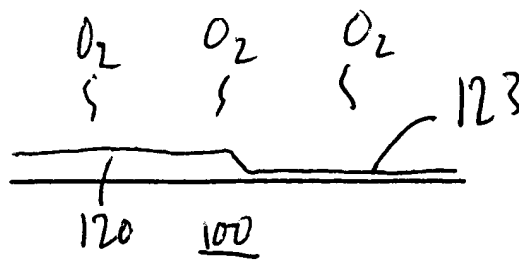


FIG. 2C

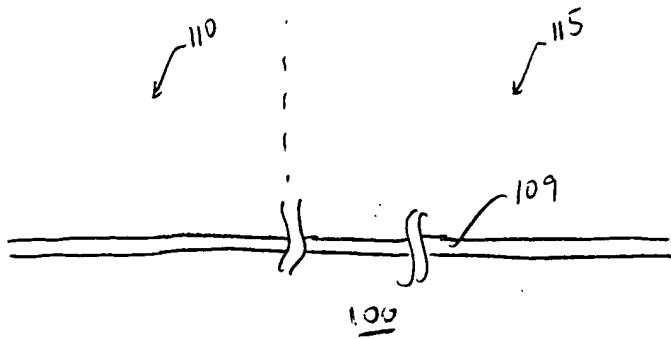


FIG. 3A

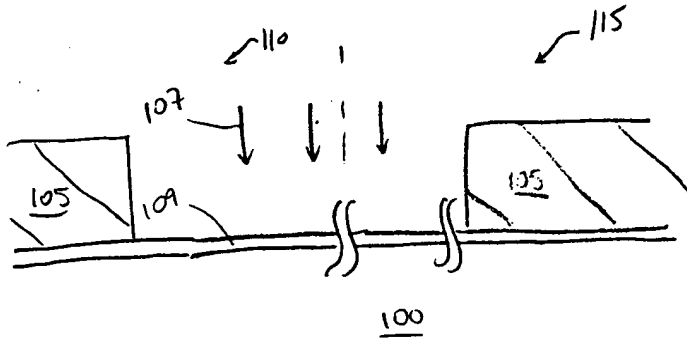


FIG. 3B

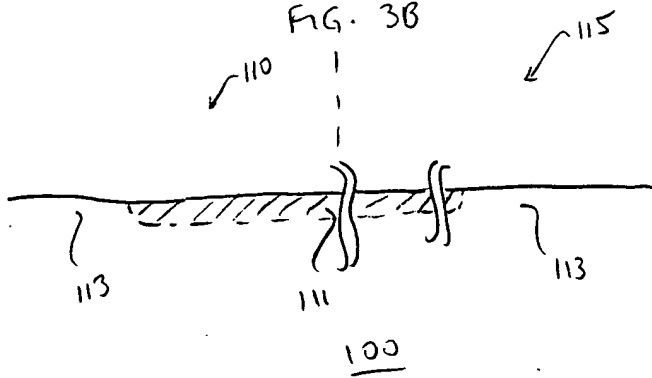


FIG. 3C

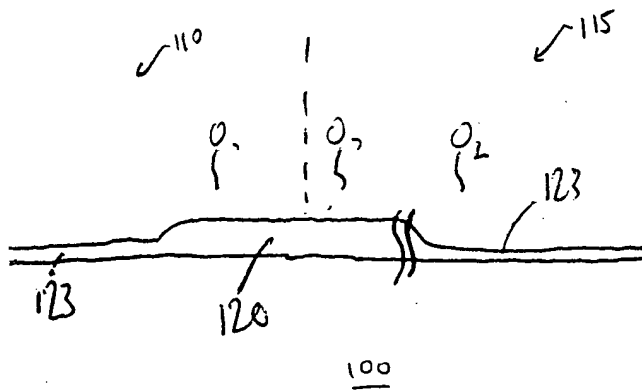


FIG. 3D

0916078 121868

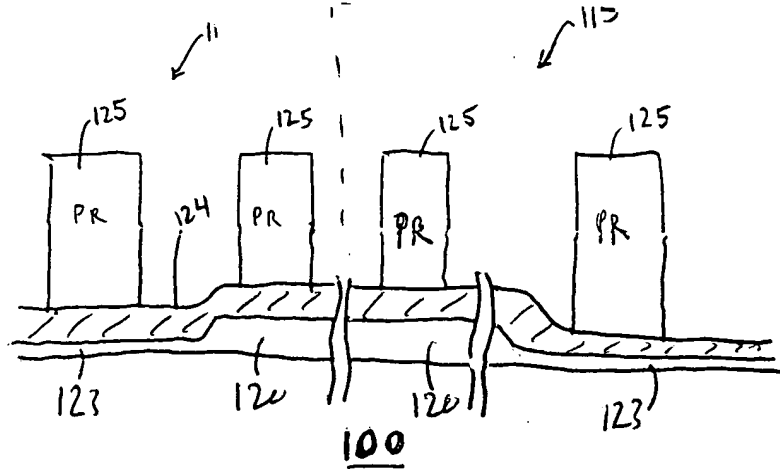


FIG. 3E

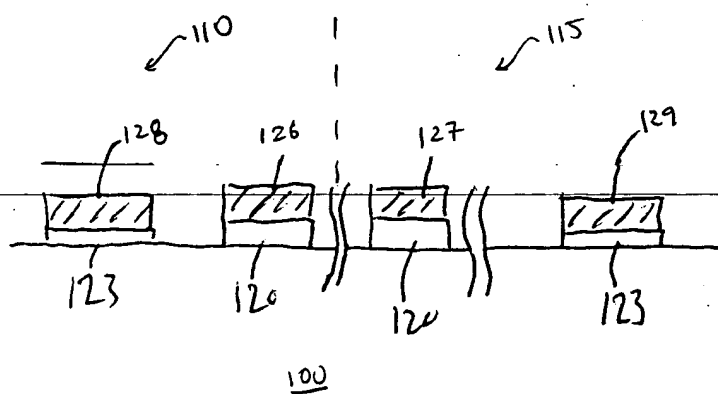


FIG. 3F

09215078-124898

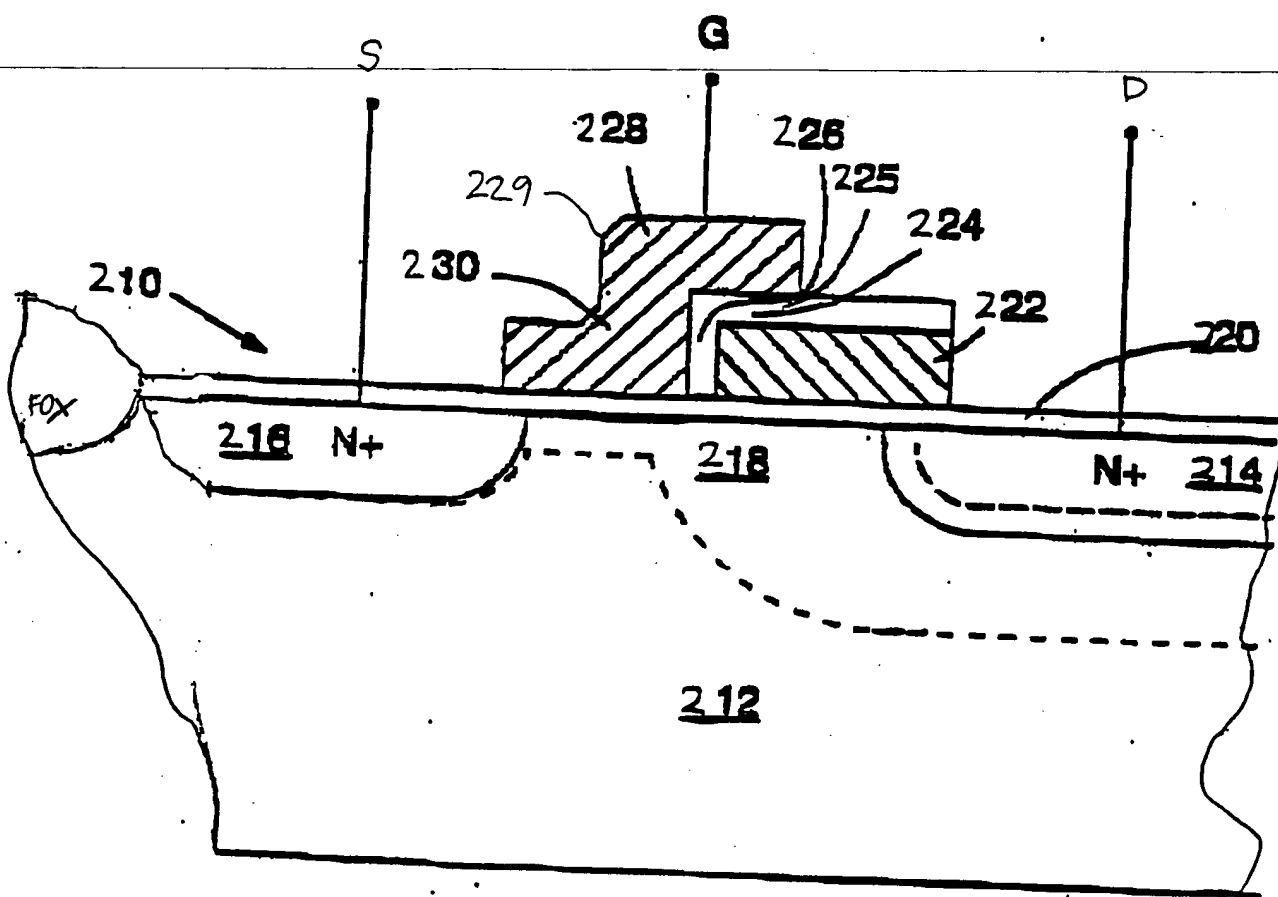
[illegible]

Fig. 4

A cross-sectional view of a semiconductor device. It shows a substrate with a trench structure. The trench has a bottom surface 313 and a side surface 331. A gate structure 329 is formed on the side surface 331. The gate structure includes a gate oxide layer 321 and a gate electrode 315. A channel region 317 is formed in the substrate between the gate electrode 315 and the bottom surface 313. A source region 327 is formed in the substrate adjacent to the gate electrode 315. A drain region 319 is formed in the substrate adjacent to the gate electrode 315. A contact pad 323 is formed on the source region 327. A contact pad 326 is formed on the drain region 319. A dashed line indicates a boundary between the source region 327 and the drain region 319.

Fig. 5

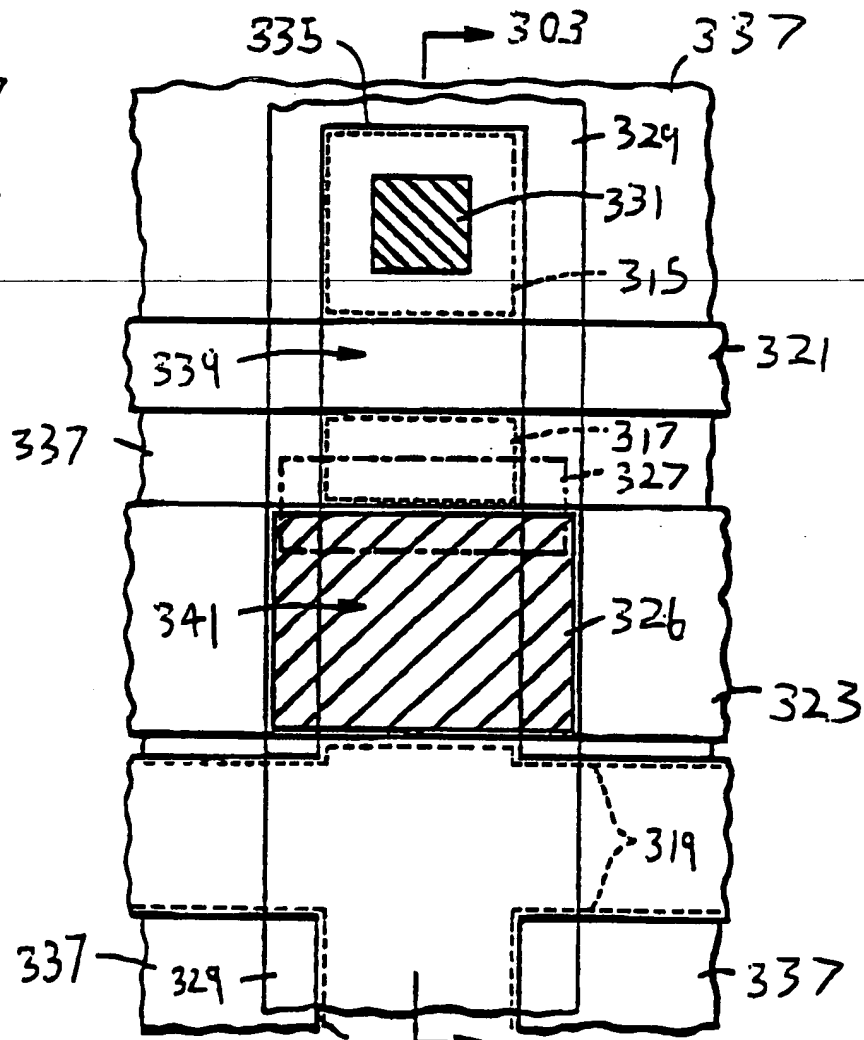


FIG. 6

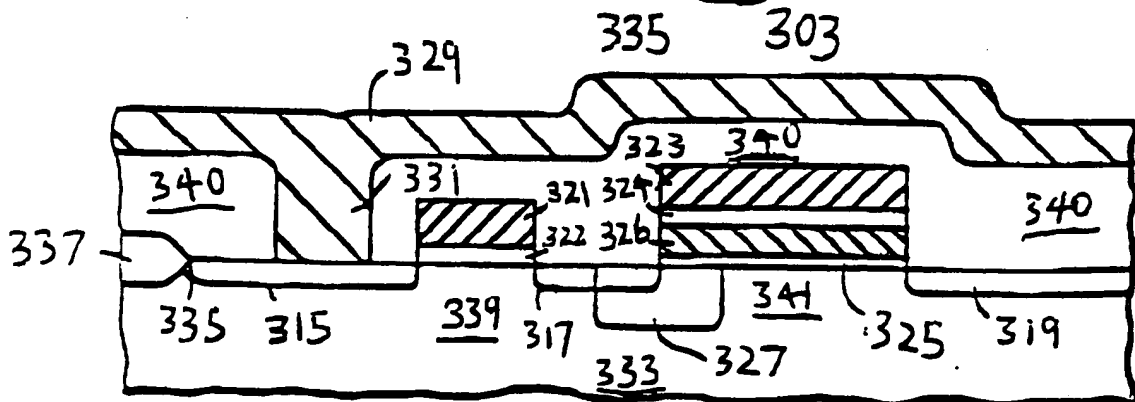


Fig 1

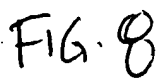
[illegible]

FIG. 8